

Sheet 1 of 1

FORM PTO 1449 (modified)

ATTY DOCKET NO 03500.016066

APPLICATION NO 10/025,928

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICELIST OF REFERENCES CITED BY APPLICANT(S)
(Use several sheets if necessary)

APPLICANT MAMORU UCHIDA

FILING DATE December 26, 2001

GROUP 2878 2878

U.S. PATENT DOCUMENTS

| *EXAMINER INITIAL | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
|----------------------|--------------------|----------|------------------|-------|----------|-------------------------------|
| PL | 5,835,646 | 11/10/98 | Yoshimura et al. | 385 | 14 | |
| PL | 6,097,472 | 8/1/00 | Tanaka et al. | 355 | 47 | |
| .PL | 2001-0032984 | 10/25/01 | Uchida | 274 | 84 | |

FOREIGN PATENT DOCUMENTS

| | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION YES/NO/ OR ABSTRACT |
|----|--------------------|----------|---------|-------|----------|---------------------------------------|
| PL | 59-75656 | 4/28/84 | Japan | | | Partial Translation and Abstract |
| PL | 8-220357 | 8/30/96 | Japan | | | Abstract |
| PL | 9-96746 | 4/8/97 | Japan | | | Abstract |
| PL | 9-270751 | 10/14/97 | Japan | | | Yes |
| PL | 10-294254 | 11/4/98 | Japan | | | Abstract |
| PL | 11-54406 | 2/26/99 | Japan | | | Abstract |
| PL | 11-72750 | 3/16/99 | Japan | | | Yes |
| PL | 11-111609 | 4/23/99 | Japan | | | Abstract |
| PL | 11-196069 | 7/21/99 | Japan | | | Abstract |
| PL | 2000-31189 | 1/28/00 | Japan | | | Abstract |
| PL | 2000-31190 | 1/28/00 | Japan | | | Abstract |
| PL | 2000-235127 | 8/29/00 | Japan | | | Abstract |
| PL | 2000-337872 | 12/8/00 | Japan | | | Abstract |
| PL | 2001-284635 | 10/12/01 | Japan | | | Abstract |

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

| | |
|----|---|
| PL | "GaN FETs For Microwave and High-temperature Applications", Steven C. Binari, K. Doverspike, G. Elner, H.B.Dietrich and A.E. Wickenden. Naval Research Laboratory, Washington, DC 20375-5320, USA |
| PL | "High-temperature Reliability of GaN Metal Semiconductor Field-Effect Transistor and Bipolar Junction Transistor" Seikoh Yoshida and Joe Suzuki, Yokohama R&D Laboratories, The Furukawa Electric Co., Ltd. 2-4-3, Okano, Nishi-ku, Yokohama, 220 Japan |

EXAMINER

DATE CONSIDERED

3/28/2003

*EXAMINER Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Sheet 1 of 1
Form #62